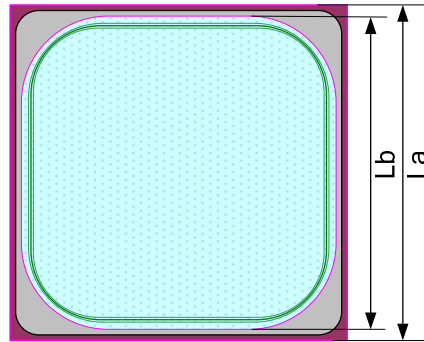


2SB075030MLJL SCHOTTKY BARRIER DIODE CHIPS

DESCRIPTION

- 2SB075030MLJL is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Low power losses, high efficiency;
- Guard ring construction for transient protection;
- Low forward voltage drop;
- High ESD capability;
- High surge capability;
- Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits.;
- Chip Size:750 μ m X 750 μ m;
- Chip Thickness: 210 \pm 20 μ m;



Chip Topography and Dimensions

La: Chip Size: 750 μ m;

Lb: Pad Size: 655 μ m;

ORDERING SPECIFICATIONS

Product Name	Specification
2SB075030MLJL	For Au and AISi wire bonding package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	30	V
Average Forward Rectified Current	IFAV	1.0	A
Peak Forward Surge Current@8.3ms	IFSM	5.5	A
Maximum Operation Junction Temperature	TJ	125	°C
Storage Temperature Range	TSTG	-40~125	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=100 μ A	30	--	V
Forward Voltage	VF1	IF=0.7A	--	0.45	V
	VF2	IF=1.0A	--	0.5	V
Reverse Current	IR	VR=30V	--	60	μ A